

NanoBridge FPGA

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Content

- Introduction & NanoBridge-FPGA
 - Energy efficient computing
 - Operation principle of NanoBridge
 - Schematic diagram of NanoBridge-FPGA
- Nonvolatile SoC-FPGA
 - Provides low power and high functionality for IoT devices
 - Accelerator of convolutional neural network (CNN)
 - 28nm NB-FPGA as accelerator
 - NanoBridge for accelerator and code ROM
- Radiation tolerance of NanoBridge
 - Demonstration of NanoBridge-FPGA on orbit
- Conclusion

Enhancement by logic architecture



Switch over logic



Switch over logic

• Integrate in BEOL (Backend-of-line) of LSI



NanoBridge[®] (or Atom switch)

- Resistive change memory (ReRAM)
- Nanometer-scale Cu bridge forms via electrochemical reaction
 - High ON/OFF ratio ~ 2k/200M Ω
 - Weak temperature dependence, Small Capacitance ~ 0.15fF
 - Reprogram cycle > 10³
 - No soft error (radiation tolerant)



Programming properties

- Program/Erase evaluation using 128kb-TEG
 - Program/Erase pulse : 1µsec or 200nsec
 - Voltage : 2V to 2.5V



Origin of current path

• Resistive switching is attributed to formation of Cu bridge.



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Temperature dependence

• nFET(Red) vs NanoBridge (Blue)



FPGA structure

• FPGA fabric consist of Configurable logic block (CLB)



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CLB for NB-FPGA

- 4 Basic logic elements (BLE)*
- BLE has 4-input LUT and DFF
- NanoBridge crossbar occupies large portion in CLB layout



SB:switch box, CB:Connection block

*X.Bai et al., VLSI Symo., 2015.

EDA tools for NB-FPGA

- Generated Configuration data from RTL code
 - STA predicts NB-FPGA performance, allowing circuits to be optimized





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Comparison with commercial low-power FPGA

16b-ALU/Signal-generator are mapped using 332 LUT



40nm SRAM-FPGA*

*http://www.latticesemi.com/Products/FPGAandCPLD/iCE40.aspx

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Power comparison



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Summary of comparison

	SRAM-FPGA	NB-FPGA
Configuration switch	SRAM/Pass Tr.	NanoBridge
Process node	40nm	40nm
# of LUTs	12.8k	6.4k
Max. speed@1.1V	28MHz	56MHz
Active energy per cycle@33MHz	66pJ	33pJ

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System-on-Chip (SoC) with ASFPGA

- Provide advanced functionality and computing power in IoT
 - Flexibility : User functions assigned to either CPU or Accelerator, depending on its computation power and functionality.
 - Reduced design complexity by using high-level logic synthesis

• Component

- Processor & Code ROM
- RAM for working memory (Flame data, Weight, etc.)
- Input / output serial port (SPI, LVDS, GPIO, etc.)
- BUS Inter-connect
- NanoBridge-FPGA
- PMU

(Power Management Unit)

CPU ↔ PMU NB-NVM ↔ NB-FPGA SPI/UART ↔ BUS GPIO ↔ DP-SRAM

Non-volatile SoC-FPGA

Deep Learning (DL) in IoT

- DL applications to IoT
 - Image/Video (Classification, object detection, scene understanding, traffic sign, etc.)
 - Natural Language (speech recognition, translation, etc.)
- Convolutional Neural Network (CNN) requires computational power
 - CNN training at cloud, CNN inference at IoT devices
- Challenges for CNN inference in IoT devices
 - Arithmetic operations / memory access
 - Power consumption / heat dissipation
 - → Accelerator with high energy efficiency



CNN accelerator comparison

- FPGA is more energy-efficient for CNN inference.
 - Benchmark : Binarized CNN (VGG16)
- Advantages of FPGA
 - No bottleneck in memory access
 - Highly energy-efficient bitwise operation
 - Massive parallel operations

Architecture	CPU (Baseline)	GPGPU	SRAM-FPGA
Device	ARM Cortex-A57	Maxwell GPU	Zynq7020
Clock Freq.	1.9 GHz	998 MHz	144 MHz
Memory	16 GB eMMC Flash	4GB LPDDR4	4.9Mb BRAM
Execution time (ms) (fps(/sec))	4,210 (0.23)	27.23 (36.7)	2.37 (421.9)
Power (W)	7	17	2.3
Efficiency (fps/W)	0.032	2.2	182.6

中原啓貴,人工知能 33巻 1号 (2018)

Power Reduction on IoT Devices

Issue 1. Processing by CPU has high latency
 →Processing time shortened by executing on FPGA
 Issue 2. <u>High leakage during standby state</u>
 → Nonvolatile FPGA power-gated by MPU



NanoBridge in FPGA & NVM

• NanoBridge for memory cell in NVM and routing switch in FPGA



Low power NVM

- Low-power read operation
 - Large ON/OFF conductance ratio : Sense amp free low operation voltage (down to 0.45V)
 - Read energy below 0.58pJ at 1.05V
 - 11nsec read access at 1.05V





CLB area shrink

- Crossbar area : -75%
 - Depopulated crossbar achieves area saving
- Logic block area : -70%



R.Nebashi et al., VLSI Symposium, 2018

FPGA specification

• Largest number of LUTs among FPGAs using novel nonvolatile memories and switches



Process	28nm CMOS with 9 metal
# of LUTs	171k
# of ASs	173 Mb
Block RAM	3.2 Mb
PLL	5
DSP	648
FPU	2
GPIO	240
LVDS	16
Core voltage	1.05 V
IO voltage	1.8 V

R.Nebashi et al., FPL, 2020

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Radiation Environments



*https://pc.watch.impress.co.jp/docs/news/event/168219.html (D.C. Matthews et al., "NSEU impact on commercial avionics", IRPS 2009.)

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Radiation Induced Effect of Si-LSI

- Single Event Effect (SEE)
 - Soft error by single high-energy particle (Heavy Ions, Neutron, Proton)
 - Single event upset (SEU)
 Bit flip in SRAM, Flip-flop
 - Single Event Latch-up (SEL)-> Hard error
 - Single Event Transient (SET)
- Total Ionizing Dose Effect (TID)
 - Hard error by accumulation of Gamma-ray
 - Induced fixed charge in MOS
 - CMOS, DRAM
- Displacement Damage Dose (DDD)
 - Hard error by large amount of Neutron
 - Displacement in lattice atom



SEE (Single event effect)

Large amount of radiations



TID (Total ionizing dose effect)

Radiation harden

- SRAM/Flash :
 - Date 0/1 is defined by Charge
 - Affected by charge induced in Si substrate
- NanoBridge :
 - ON/OFF states are defined by physical metallic wire
 - not affected by induced charge





Summary of experimental results

Effect	Radiation	Source	Energy	Dose	DUT	Active	Judge
SEU	Neutron	Acc./Be	2MeV	3.6e11	NB-FPGA	Dynamic	ОК
SEU	Neutron	Acc./Be	2MeV	1.2e12	NB-FPGA	Static	ОК
SEU	Heavy lon	Cf-252	30 MeV/cm ² /mg	2.7e5	NB-FPGA	Dynamic	ОК
SEU	Heavy lon	Acc. /Xe	68.9 MeV/cm²/mg	2e7	NB-FPGA	Dynamic	ОК
SEU	α-ray	Am	5.4MeV	1.1e8	NB-FPGA	Dynamic	ОК
TID	Gamma- ray	Co60	1MeV	5kGy	NanoBridge	Static	ОК
TID	Gamma- ray	Co60	1MeV	10kGy	NB-FPGA	Static	Static current increase
DDD	Neutron	Nuclear reactor	<2MeV	1e14	NanoBridge	Static	ОК

K.Ueno et al., IEEE NSS 2021

T.Sakamoto et al., Memrisys 2021 Page : 29

Experimental Results in RAPIS-I

• No error detected

- Soft error detection circuit
 Operation time > 3,300 hours
- Image total : 280 pics.





DUT Type	Scale	Duration (hours)	SEU counts
BRAM	2kbit	859	0
AS-Chain1	96 CLBs	2,254	0
AS-Chain2	368 CLBs	230	0
DFF/AS-Chain	468 CLBs	45	0

Conclusion

• Low power of NanoBridge-FPGA demonstrated

- NB-FPGA with 171k LUT for CNN accelerator
 - Depopulated crossbar achieves 75% area saving
 - CNN can be applied to 28nm NB-FPGA
- Radiation tolerance of NanoBridge-FPGA
 - Free from single event upset (SET) & Total ion dose effect (TID)
 - Successful 1 year operation in space

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